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Docket No. 0819-0425

UPC 811

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

)

Haruko INOUE et al.

) Group Art Unit: 2811

Serial No. 09/666,156

) Examiner: S. Loke

Filed: September 19, 2000

)

For: HIGH-VOLTAGE MOS

)

TRANSISTOR AND METHOD

)

FOR FABRICATING THE SAME

)

**CERTIFICATE OF MAILING**

I hereby certify that this correspondence is being deposited with The United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on 3/16/02

**RESPONSE TO ELECTION REQUIREMENT**

Honorable Commissioner for Patents

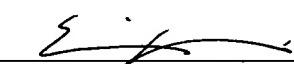
Washington, D.C. 20231

Sir:

In response to the election requirement in the Office Action of February 20, 2002, Applicants hereby elect without traverse the Group I claims - that is, claims 1-7, drawn to a semiconductor device.

Examination on the merits is requested.

Respectfully submitted,

  
Eric J. Robinson  
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